

FORM PTO-1449 (SUBSTITUTE)		Attorney Docket No.: P2001,0387 Appl. No.:	
U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		Applicant: GABRIELE FICHTL ET AL.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))		Filing Date: November 17, 2003 Group Art Unit:	

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
<i>Al</i>	A	5,871,659	2/16/99	Sakano et al.			
	B	5,719,080	2/17/98	Kenney			
	C	6,221,784 B1	4/24/01	Schmidt et al.			
	D	5,998,821	12/7/99	Hieda et al.			
	E	5,423,941	6/13/95	Komura et al.			
<i>Al</i>	F	6,583,020 B2	6/24/03	Uhlig et al.			
	G						
	H						
	I						

## FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES   NO
<i>Al</i>	J	00/54326	9/14/00	WIPO			
	K	63240027	10/5/88	Japan			
	L	10022271	1/23/98	Japan			
<i>Al</i>	M	0 819 786 A2	1/21/98	Europe			
	N						

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

<i>Al</i>		Author not listed: "Process for Simultaneously Forming Poly/EPI Silicon Filled Deep and Shallow Isolation Trenches Having a CVD Oxide Cap", IBM Technical Disclosure Bulletin, IBM Corp., Vol. 33, No. 7; December 1990 pp. 388-392

EXAMINER	DATE CONSIDERED
<i>Andy, Murali</i>	05/28/04